Vishay Semiconductors



FEATURES • Ultrafast recovery time, reduced Q_{rr} and soft

- recovery 175 °C maximum operating junction temperature
- For PFC CRM/CCM, snubber operation
- · Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

State of the art ultrafast recovery rectifiers designed with optimized performance of forward voltage drop, ultrafast recovery time, and fast recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC Boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

MECHANICAL DATA

Case: SMB (DO-214AA)

Molding compound meets UL 94 V-0 flammability rating Halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per J-STD-002

Polarity: color band denotes the cathode end

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage	V _{RRM}		600	V
Average rectified forward current	I _{F(AV)}	$T_{L} = 110 \ ^{\circ}C \ ^{(1)}$	3	٨
Non-repetitive peak surge current per leg	I _{FSM}	$T_J = 25 \ ^{\circ}C$, 6 ms square pulse	55	A
Operating junction and storage temperatures	T _J , T _{Stg}		-55 to +175	°C

Note

⁽¹⁾ Mounted on PCB with minimum pad size

ELECTRICAL SPECIFICATIONS ($T_J = 25$ °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V_{BR}, V_{R}	I _R = 100 μA	600	-	-		
Forward voltage	V _F	I _F = 3 A	-	1.15	1.35	V	
r orward voltage	۷F	I _F = 3 A, T _J = 150 °C	-	0.99	1.2		
Reverse leakage current		$V_{R} = V_{R}$ rated	-	-	3		
neverse leakage current	IR	$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	-	100	μA	
Junction capacitance	CT	V _R = 600 V	-	3.9	-	pF	

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LINKS TO ADDITIONAL RESOURCES

PRIMARY CHARACTERISTICS



SMB (DO-214AA)

I_{F(AV)}

 V_{R}

V_F at I_F

t_{rr} typ.

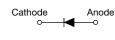
T_J max.

Package

Circuit configuration

30

3D Models



3 A

600 V

0.99 V

41 ns

175 °C

SMB (DO-214AA)

Single



RoHS COMPLIANT

HALOGEN

FREE



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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		I _F = 1.0 A, dI _F /dt =	100 A/ μ s, V _R = 30 V	-	41	-	
		I _F = 1.0 A, dI _F /dt =	50 A/ μ s, V _R = 30 V	-	52	-	
Reverse recovery time	t _{rr}	I _F = 0.5 A, I _R = 1 A	, I _{rr} = 0.25 A	-	-	65	ns
		T _J = 25 °C		-	38	-	
		T _J = 125 °C		-	52	-	
Deels receiver a urrent		T _J = 25 °C	$I_F = 3 A$	-	5.6	-	٨
Peak recovery current	I _{RRM}	T _J = 125 °C	dl _F /dt = 200 A/µs V _B = 390 V	-	7.3	-	A
	0	T _J = 25 °C		-	108	-	
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	193	-	nC

THERMAL - MECHANICAL SF	PECIFICAT	TIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	+175	°C
Thermal resistance, junction to mount	R _{thJM} ⁽¹⁾		-	-	18	°C/W
Thermal resistance, junction to ambient	R _{thJA} ⁽¹⁾		-	-	90	0/10
Approximate Weight				0.1		g
Approximate weight				0.003		oz.
Marking device		Case style SMB (DO-214AA)		3U	6H	

Note

⁽¹⁾ Mounted on PCB with minimum pad size

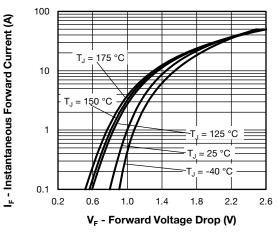


Fig. 1 - Typical Forward Voltage Drop Characteristics

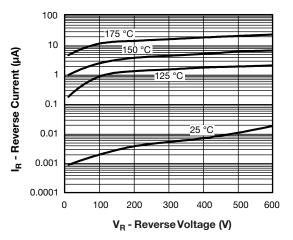
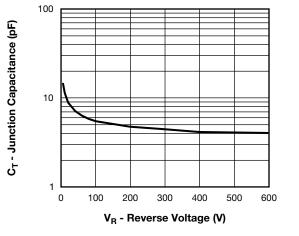


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



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Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

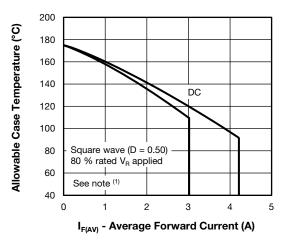
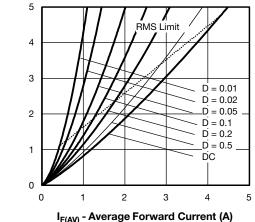


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current



Average Power Loss (W)

F(AV) - Average i of ward outlent (A)

Fig. 5 - Forward Power Loss Characteristics

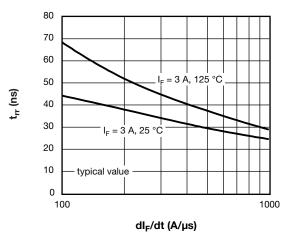


Fig. 6 - Typical Reverse Recovery Time vs. dI_F/dt

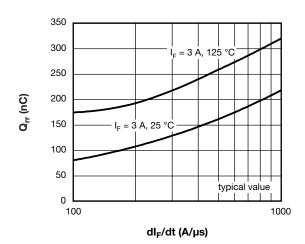


Fig. 7 - Typical Stored Charge vs. dl_F/dt

Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

 $\begin{array}{l} \mathsf{Pd} = \mathsf{forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \ \mathsf{x} \ \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{5}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \ \mathsf{x} \ \mathsf{I}_{\mathsf{R}} \ (1 - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

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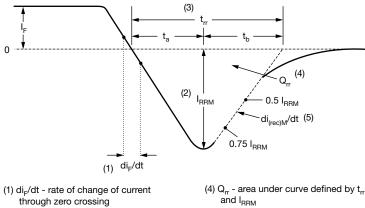
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VS-3EGU06WHM3

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- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{\rm rr}$ reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

and I_{RRM}

 $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$

(5) di(rec)M/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 8 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

SHAY

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Device code	VS-	3	Е	G	U	06	W	н	М3
	1	2	3	4	5	6	7	8	9
	1 ·	· Visl	nay Sen	niconduo	ctors pro	oduct			
	2 -	- Cur	rent rati	ng (3 = 3	3 A)				
	3 -	· Circ	uit conf	iguratior	ר:				
		E =	single o	liode					
	4 -	- G =	SMB p	ackage					
	5 -	· Pro	cess typ	e,					
		U =	ultrafas	t recove	ery				
	6 -	· Volt	age coo	de (06 =	600 V)				
	7 -	• W =	specia	I					
	8 -	- H=	AEC-Q	101 qua	lified				
	9 -	• МЗ	= halog	en-free,	RoHS-o	complia	nt, and	terminat	tions lea

ORDERING INFORMATI	ON (Example)		
PREFERRED P/N	PACKAGE CODE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION
VS-3EGU06WHM3/5BT	5BT	3200	13"diameter plastic tape and reel

LINKS TO RELATED DOCUMENTS			
Dimensions	www.vishay.com/doc?95401		
Part marking information	www.vishay.com/doc?95624		
Packaging information	www.vishay.com/doc?95404		
SPICE model	www.vishay.com/doc?96667		

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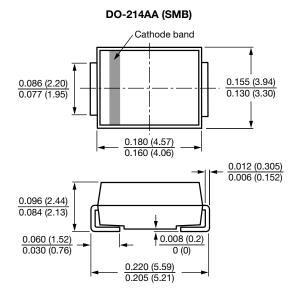


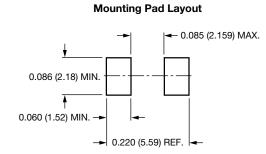
Outline Dimensions

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SMB

DIMENSIONS in inches (millimeters)







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